

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 124231		APPLICATION NO. New U.S. National Stage of PCT/IP03/016794 <div style="font-size: 1.2em; font-weight: bold;">10/538878</div>	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Masahiro SAKURADA et al.			
				FILING DATE June 14, 2005		GROUP 1702	

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	

FOREIGN PATENT DOCUMENTS						
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS		
FH. 1 JP A 2000-351690 w/ abst & transl	12/19/2000	JAPAN	—	—		
FH. 2 JP A 2000-178099 w/ abst & transl	6/27/2000	JAPAN	—	—		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
FH.	3	VORONKOV, "The Mechanism of Swirl Defects Formation in Silicon," <i>Journal of Crystal Growth</i> , vol. 59, no. 3, pp. 625-643 {March 1, 1982}
FH.	4	DUPRET et al., "Global Modelling of Heat Transfer in Crystal Growth Furnaces," <i>Int. J. Heat Mass Transfer</i> , vol. 33, no. 9, pp. 1849-1871 {April 7, 1998}

EXAMINER <i>[Signature]</i>	DATE CONSIDERED <i>6/17/2006</i>
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Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Date: June 14, 2005